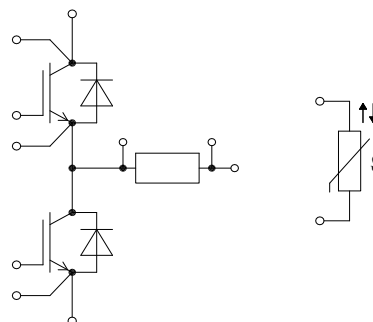


EconoDUAL™3 模块 采用第四代沟槽栅/场终止IGBT4和HE型发射极控制二极管
带有pressfit压接管脚和温度检测NTC和电流采样电阻

EconoDUAL™3 module with Trench/Fieldstop IGBT4 and Emitter Controlled HE diode and PressFIT / NTC / current sense shunt



Typical Appearance



$V_{CES} = 1200V$
 $I_{C\ nom} = 300A / I_{CRM} = 600A$

潜在应用

- UPS系统
- 伺服驱动器
- 大功率变流器
- 电机传动
- 风力发电机

Potential Applications

- UPS systems
- Servo drives
- High power converters
- Motor drives
- Wind turbines

电气特性

- $T_{vj\ op} = 150^{\circ}C$
- V_{CESat} 带正温度系数
- 低 V_{CESat}
- 集成电流传感器

Electrical Features

- $T_{vj\ op} = 150^{\circ}C$
- V_{CESat} with positive temperature coefficient
- Low V_{CESat}
- Integrated current sensor

机械特性

- PressFIT 压接技术
- 绝缘的基板
- 预涂导热介质
- 高功率密度

Mechanical Features

- PressFIT contact technology
- Isolated base plate
- Pre-applied Thermal Interface Material
- High power density

Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

IGBT, 逆变器 / IGBT, Inverter

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{CES}	1200	V
连续集电极直流电流 Continuous DC collector current	$T_H = 70^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$	300	A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	I_{CRM}	600	A
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

		min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 300\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 300\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 300\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,75 2,00 2,05	2,10 V V V
栅极阈值电压 Gate threshold voltage	$I_C = 11,5\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$	V_{GEth}	5,25	5,80	6,45 V
栅极电荷 Gate charge	$V_{GE} = -15 / 15\text{ V}$	Q_G	2,25		μC
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$	R_{Gint}	2,5		Ω
输入电容 Input capacitance	$f = 1000\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$	C_{ies}	18,5		nF
反向传输电容 Reverse transfer capacitance	$f = 1000\text{ kHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$	C_{res}	1,05		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$	I_{CES}		3,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$	I_{GES}		400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 300\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 1,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{don}	0,15 0,17 0,17	μs μs μs
上升时间(电感负载) Rise time, inductive load	$I_C = 300\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Gon} = 1,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_r	0,05 0,05 0,05	μs μs μs
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 300\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 1,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_{doff}	0,35 0,45 0,48	μs μs μs
下降时间(电感负载) Fall time, inductive load	$I_C = 300\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = -15 / 15\text{ V}$ $R_{Goff} = 1,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	t_f	0,10 0,20 0,24	μs μs μs
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 300\text{ A}, V_{CE} = 600\text{ V}, L\sigma = 35\text{ nH}$ $di/dt = 5550\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Gon} = 1,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{on}	18,0 30,0 34,0	mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 300\text{ A}, V_{CE} = 600\text{ V}, L\sigma = 35\text{ nH}$ $du/dt = 3250\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $V_{GE} = -15 / 15\text{ V}, R_{Goff} = 1,3\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{off}	22,0 36,0 40,0	mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$	I_{SC}	1200		A
结 - 散热器热阻 Thermal resistance, junction to heatsink	每个 IGBT / per IGBT valid with IFX pre-applied thermal interface material	R_{thJH}		0,136	K/W
在开关状态下温度 Temperature under switching conditions		$T_{vj\text{op}}$	-40	150	$^{\circ}\text{C}$

二极管, 逆变器 / Diode, Inverter 最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	300	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	I_{FRM}	600	A
I ² t-值 I ² t - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	I^2t	18500 17900	A ² s A ² s

特征值 / Characteristic Values

		min.	typ.	max.	
正向电压 Forward voltage	$I_F = 300\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 300\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 300\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	V_F	1,65 1,65 1,65	2,10 V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 300\text{ A}, -di_F/dt = 5550\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	I_{RM}	250 305 320	A A A
恢复电荷 Recovered charge	$I_F = 300\text{ A}, -di_F/dt = 5550\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	Q_r	31,5 61,0 70,0	μC μC μC
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 300\text{ A}, -di_F/dt = 5550\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	E_{rec}	14,0 26,5 30,0	mJ mJ mJ
结 - 散热器热阻 Thermal resistance, junction to heatsink	每个二极管 / per diode valid with IFX pre-applied thermal interface material		R_{thJH}		0,177 K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150 $^{\circ}\text{C}$

电流取样电阻 / Shunt

		min.	typ.	max.	
额定电阻值 Rated resistance	$T_H = 20^{\circ}\text{C}$	R_{20}	0,50		m Ω
温度系数(tcr) Temperature coefficient (tcr)	$20^{\circ}\text{C} - 60^{\circ}\text{C}$		< 30		ppm/K
负载能力, 每个电流取样电阻 Load capacity per shunt-resistor	$T_H = 80^{\circ}\text{C}$	P		27	W
电流取样电阻工作温度 Operation temperature shunt-resistor		$T_{tvj\text{ op}}$		200	$^{\circ}\text{C}$
结 - 散热器热阻 Thermal resistance, junction to heatsink	pro Shunt-Widerstand / per shunt-resistor valid with IFX pre-applied thermal interface material	R_{thJH}		4,3	K/W

负温度系数热敏电阻 / NTC-Thermistor

特征值 / Characteristic Values

		min.	typ.	max.	
额定电阻值 Rated resistance	$T_{NTC} = 25^{\circ}\text{C}$	R_{25}	5,00		k Ω
R100 偏差 Deviation of R100	$T_{NTC} = 100^{\circ}\text{C}, R_{100} = 493\ \Omega$	$\Delta R/R$	-5	5	%
耗散功率 Power dissipation	$T_{NTC} = 25^{\circ}\text{C}$	P_{25}		20,0	mW
B-值 B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/50}$	3375		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/80}$	3411		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$	$B_{25/100}$	3433		K

根据应用手册标定

Specification according to the valid application note.

模块 / Module

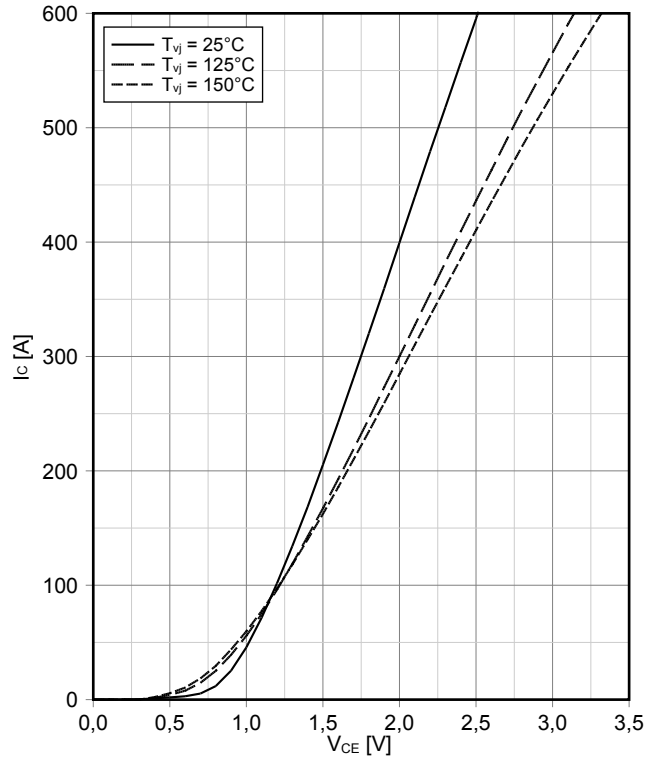
绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min	V _{ISOL}	2,5		kV
模块基板材料 Material of module baseplate			Cu		
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al ₂ O ₃		
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		14,5 13,0		mm
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		12,5 10,0		mm
相对电痕指数 Comperative tracking index		CTI	> 200		
			min.	typ.	max.
杂散电感, 模块 Stray inductance module		L _{sCE}		20	nH
模块引线电阻, 端子-芯片 Module lead resistance, terminals - chip	T _H = 25°C, 每个开关 / per switch	R _{CC+EE'}		1,00	mΩ
储存温度 Storage temperature		T _{stg}	-40		125 °C
最高基板工作温度 Maximum baseplate operation temperature		T _{BPmax}			125 °C
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M5 根据相应的应用手册进行安装 Screw M5 - Mounting according to valid application note	M	3,00		6,00 Nm
端子联接扭矩 Terminal connection torque	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	3,0	-	6,0 Nm
重量 Weight		G		345	g

Lagerung und Transport von Modulen mit TIM => siehe AN2012-07
Storage and shipment of modules with TIM => see AN2012-07

输出特性 IGBT, 逆变器 (典型)

output characteristic IGBT, Inverter (typical)

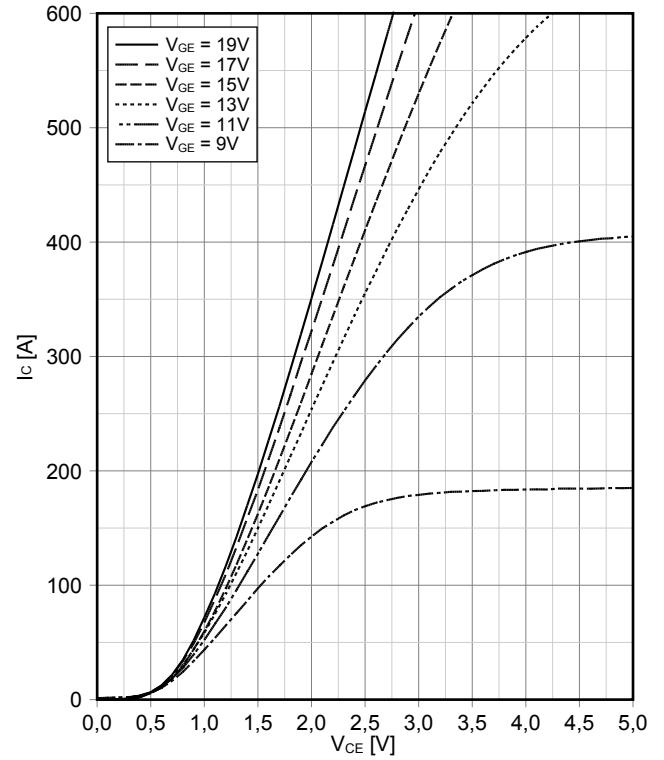
$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



输出特性 IGBT, 逆变器 (典型)

output characteristic IGBT, Inverter (typical)

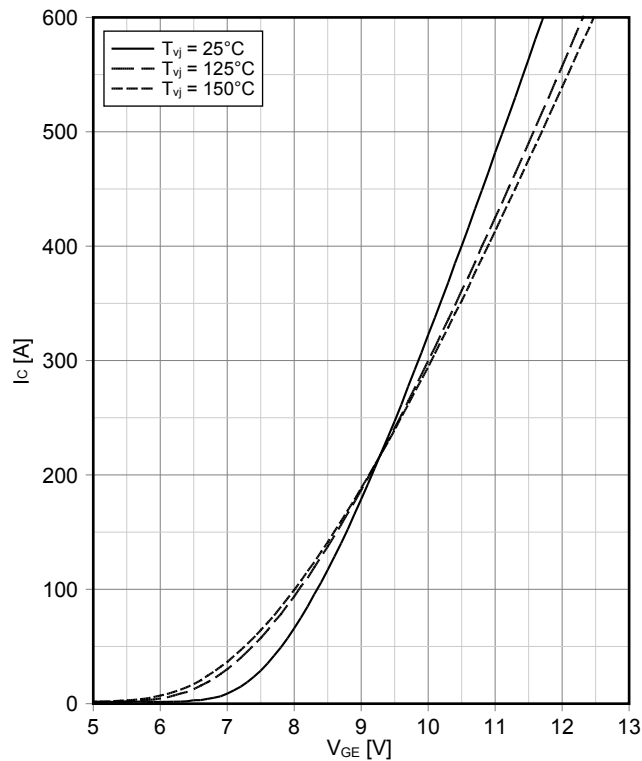
$I_C = f(V_{CE})$
 $T_{vj} = 150^\circ\text{C}$



传输特性 IGBT, 逆变器 (典型)

transfer characteristic IGBT, Inverter (typical)

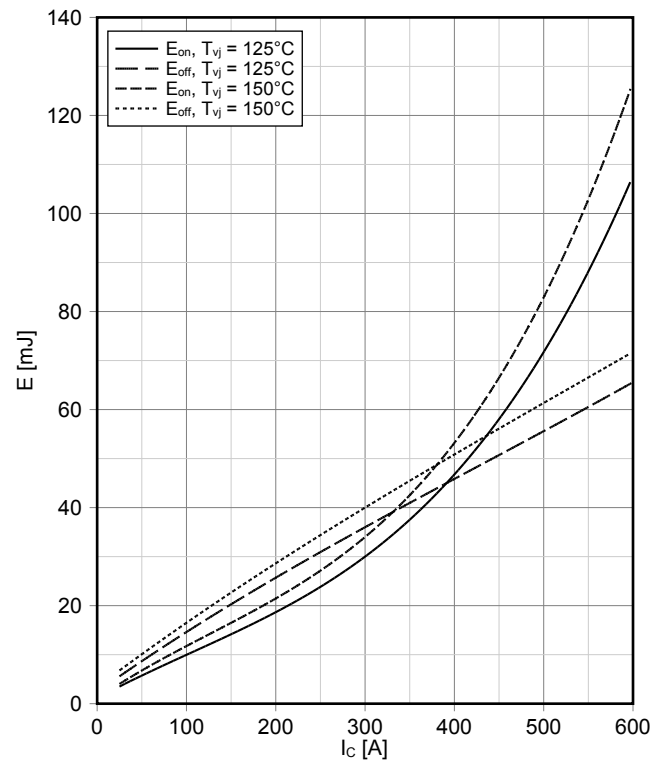
$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



开关损耗 IGBT, 逆变器 (典型)

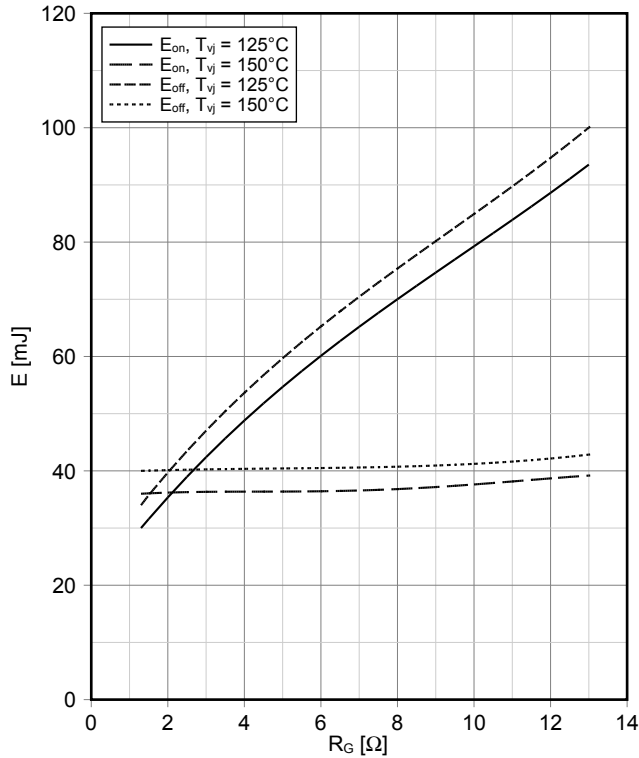
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 1.3\ \Omega$, $R_{Goff} = 1.3\ \Omega$, $V_{CE} = 600\text{ V}$

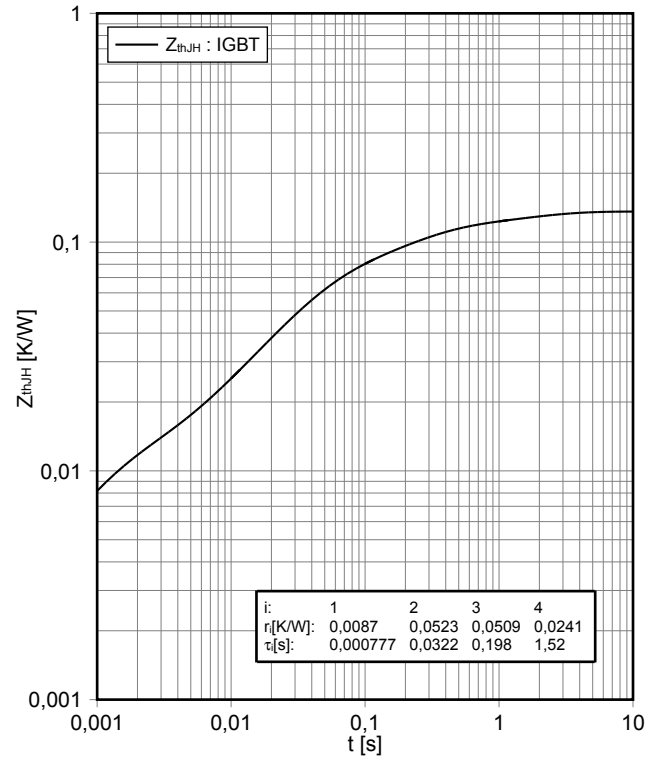


开关损耗 IGBT, 逆变器 (典型)
switching losses IGBT, Inverter (typical)

$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 300\text{ A}$, $V_{CE} = 600\text{ V}$

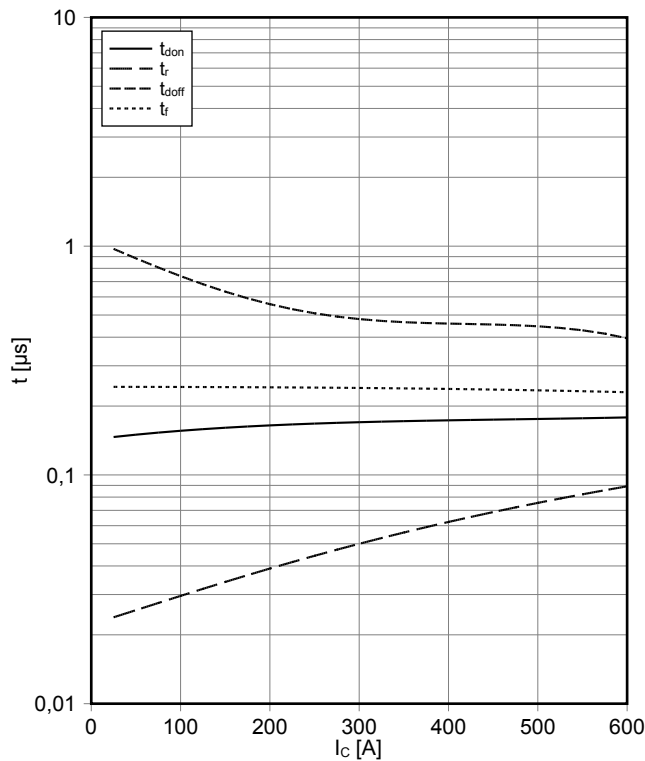


瞬态热阻抗 IGBT, 逆变器
transient thermal impedance IGBT, Inverter
 $Z_{thJH} = f(t)$



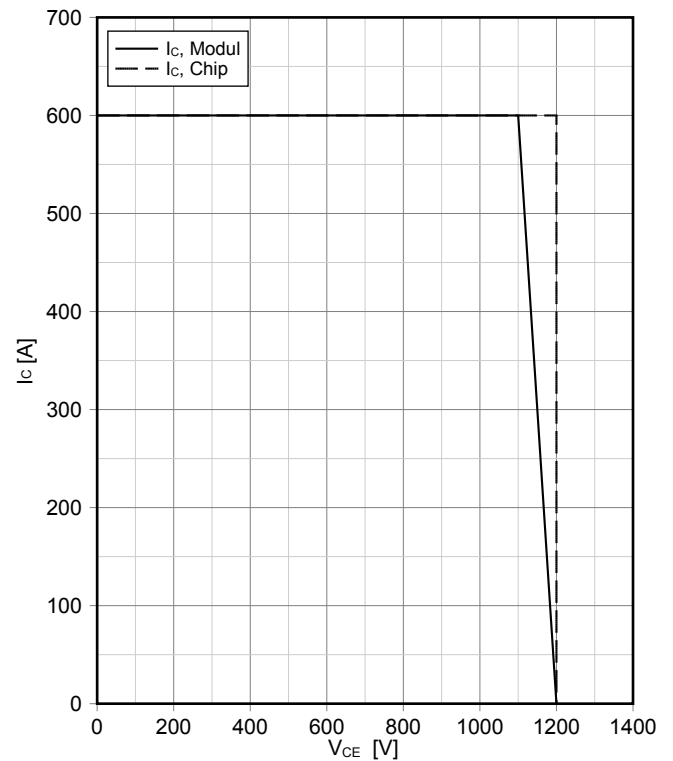
??? IGBT, 逆变器 (典型)
switching times IGBT, Inverter (typical)

$t_{don} = f(I_C)$, $t_r = f(I_C)$, $t_{doff} = f(I_C)$, $t_f = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 1.3\ \Omega$, $R_{Goff} = 1.3\ \Omega$, $V_{CE} = 600\text{ V}$



反偏安全工作区 IGBT, 逆变器 (RBSOA)
reverse bias safe operating area IGBT, Inverter (RBSOA)

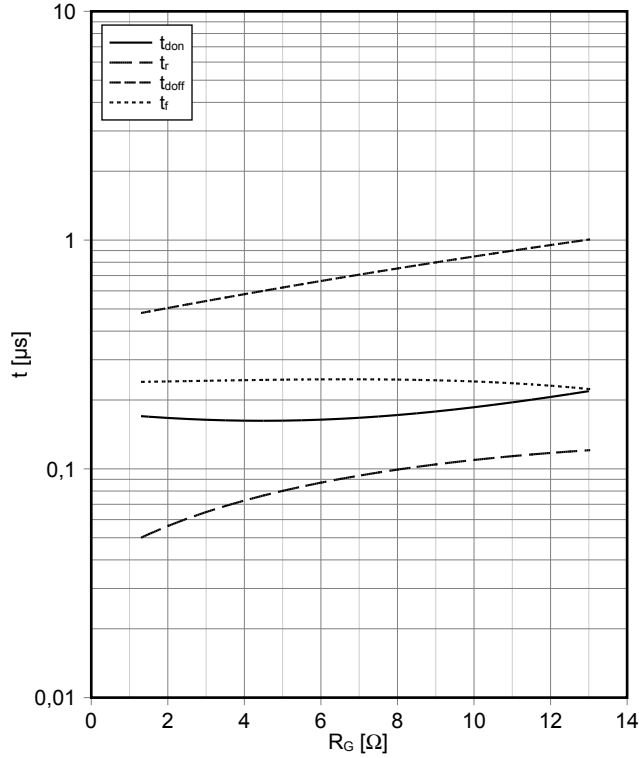
$I_C = f(V_{CE})$
 $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 1.3\ \Omega$, $T_{vj} = 150^\circ\text{C}$



??? IGBT, 逆变器 (典型)

switching times IGBT, Inverter (typical)

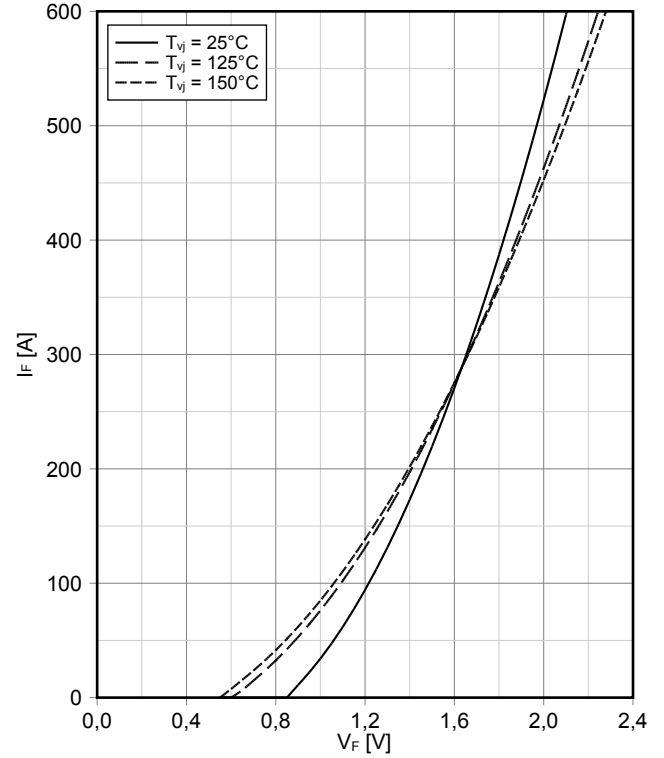
$t_{don} = f(R_G), t_r = f(R_G), t_{doff} = f(R_G), t_f = f(R_G)$
 $V_{GE} = \pm 15\text{ V}, I_C = 300\text{ A}, V_{CE} = 600\text{ V}, T_{vj} = 150^\circ\text{C}$



正向偏压特性 二极管, 逆变器 (典型)

forward characteristic of Diode, Inverter (typical)

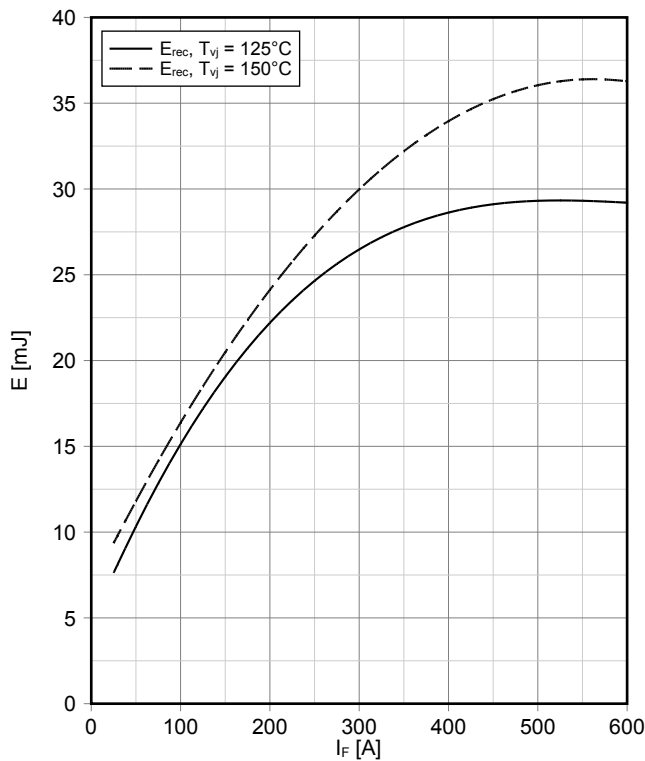
$I_F = f(V_F)$



开关损耗 二极管, 逆变器 (典型)

switching losses Diode, Inverter (typical)

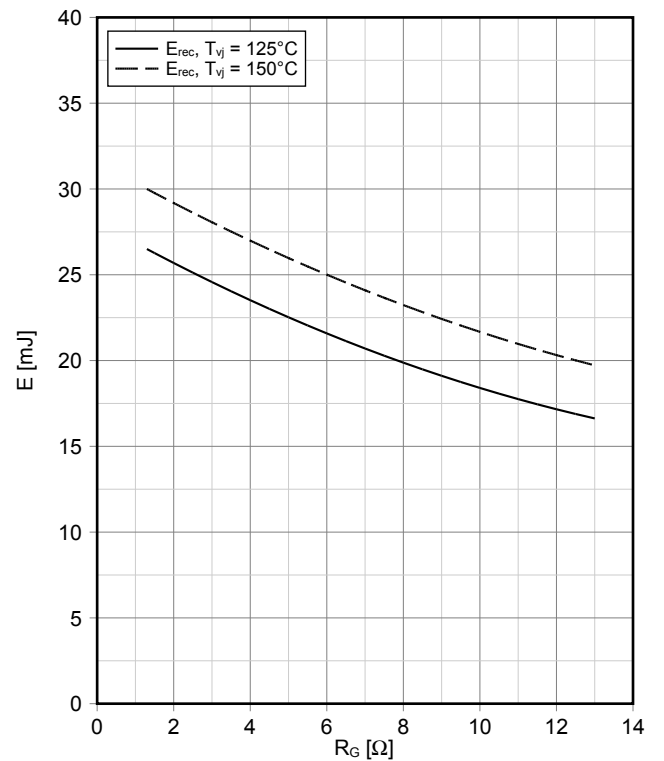
$E_{rec} = f(I_F)$
 $R_{Gon} = 1.3\ \Omega, V_{CE} = 600\text{ V}$



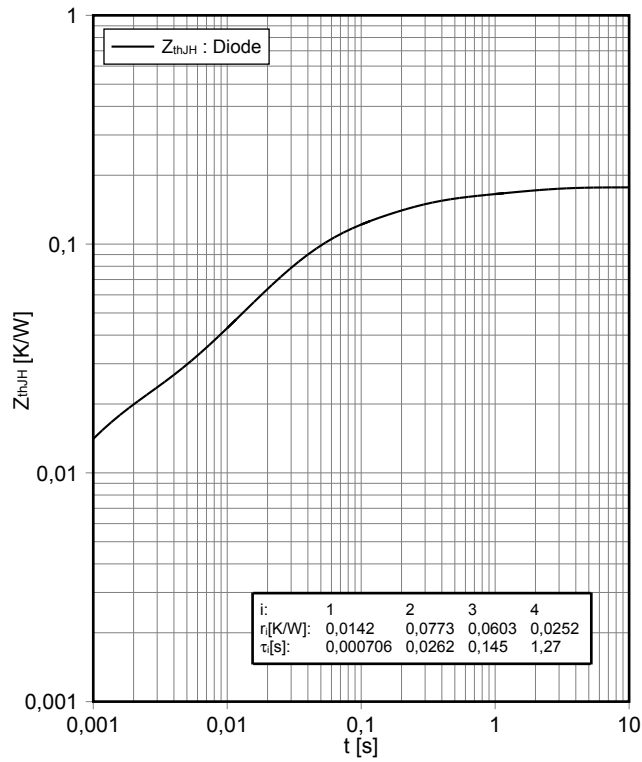
开关损耗 二极管, 逆变器 (典型)

switching losses Diode, Inverter (typical)

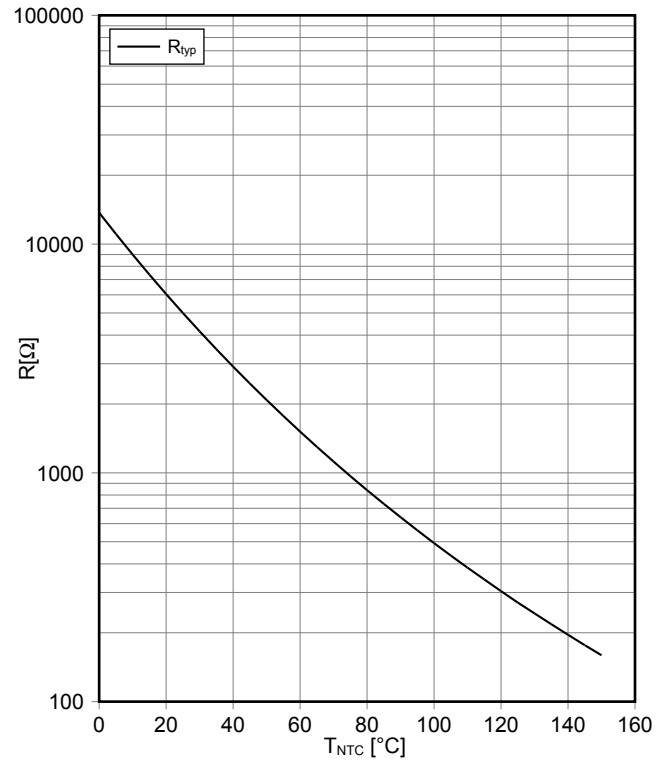
$E_{rec} = f(R_G)$
 $I_F = 300\text{ A}, V_{CE} = 600\text{ V}$



瞬态热阻抗 二极管, 逆变器
transient thermal impedance Diode, Inverter
 $Z_{thJH} = f(t)$



负温度系数热敏电阻 温度特性
NTC-Thermistor-temperature characteristic (typical)
 $R = f(T)$



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